

September 2007

# **FDG6342L**

# **Integrated Load Switch**

### **Features**

- Max  $r_{DS(on)} = 150m\Omega$  at  $V_{GS} = 4.5V$ ,  $I_D = -1.5A$
- Max  $r_{DS(on)} = 195m\Omega$  at  $V_{GS} = 2.5V$ ,  $I_D = -1.3A$
- Max  $r_{DS(on)} = 280 \text{m}\Omega$  at  $V_{GS} = 1.8 \text{V}$ ,  $I_D = -1.1 \text{A}$
- Max  $r_{DS(on)} = 480 \text{m}\Omega$  at  $V_{GS} = 1.5 \text{V}$ ,  $I_D = -0.9 \text{A}$
- Control MOSFET (Q1) includes Zener protection for ESD ruggedness (>4KV Human body model)
- High performance trench technology for extremely low r<sub>DS(on)</sub>
- Compact industry standard SC70-6 surface mount package
- RoHS Compliant

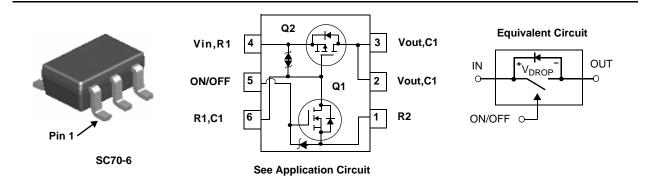


### **General Description**

This device is particularly suited for compact power management in portable electronic equipment where 1.5V to 8V input and 1.5A output current capability are needed. This load switch integrates a small N-Channel power MOSFET (Q1) that drives a large P-Channel power MOSFET (Q2) in one tiny SC70-6 package.

# **Applications**

- Power management
- Load switch



# **MOSFET Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>IN</sub>	Gate to Source Voltage (Q2)		±8	V
V <sub>ON/OFF</sub>	Gate to Source Voltage (Q1)		-0.5 to 8	V
I <sub>Load</sub>	Load Current -Continuous	(Note 2)	-1.5	^
	-Pulsed	(Note 2)	-6	A
D	Power Dissipation for Single Operation	(Note 1a)	0.36	W
$P_D$		(Note 1b)	0.3	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1a)	350	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1b)	415	*C/VV

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Package Reel Size		Quantity	
.42	FDG6342L	SC70-6	7"	8mm	3000units	

# **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted Parameter

Off Characteristics						
$BV_{IN}$	V <sub>IN</sub> Breakdown Voltage	$I_D = -250 \mu A, V_{ON/OFF} = 0 V$	8			V
I <sub>Load</sub>	Zero Gate Voltage Drain Current	$V_{IN} = -6.4V$ , $V_{ON/OFF} = 0V$			-1	μА
I <sub>FL</sub>	Leakage Current, Forward	$V_{IN} = 8V, V_{ON/OFF} = 0V$			10	μА
I <sub>RL</sub>	Leakage Current, Reverse	$V_{IN} = -8V$ , $V_{ON/OFF} = 0V$			-10	μΑ

**Test Conditions** 

Min

Max

Тур

Units

## On Characteristics (note 2)

Symbol

V <sub>ON/OFF(th)</sub>	Gate Threshold Voltage	$V_{IN} = V_{ON/OFF}, I_D = -250\mu A$	0.65	0.8	1.5	V
	Static Drain to Source On Resistance (Q2)  Static Drain to Source On Resistance (Q1)	$V_{IN} = 4.5V, I_D = -1.5A$		125	150	mΩ
		$V_{IN} = 2.5V, I_D = -1.3A$		150	195	
r <sub>DS(on)</sub>		$V_{IN} = 1.8V, I_D = -1.1A$		200	280	
		$V_{IN} = 1.5V, I_D = -0.9A$		250	480	
		$V_{IN} = 4.5V, I_D = 0.4A$		2.6	4.0	Ω
		$V_{IN} = 2.7V, I_D = 0.2A$		3.3	5.0	22

## **Drain-Source Diode Characteristics**

Ī	l <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current			-0.25	V
,	$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{ON/OFF} = 0V, I_S = -0.25A \text{ (Note 2)}$	-0.6	-1.2	V

1.  $R_{\theta JA}$  is determined with the device mounted on a 1in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



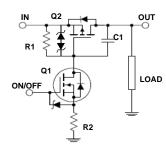
a. 350°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b. 415°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width <  $300\mu$ s, Duty cycle < 2.0%.

## FDG6342LLoad Switch Application circuit



### **External Component Recommendation:**

For additional in-rush current control, R2 and C1 can be added. For more information, see application note AN1030

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

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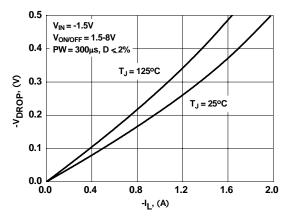


Figure 1. Conduction Voltage Drop Variation with Load Current.

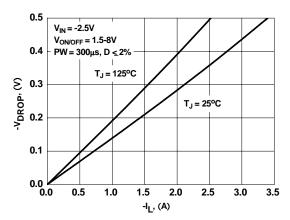


Figure 3. Conduction Voltage Drop Variation with Load Current.

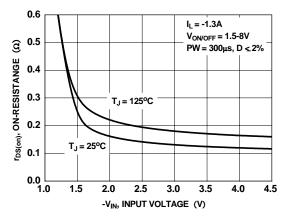


Figure 5. On-Resistance Variation With Input Voltage

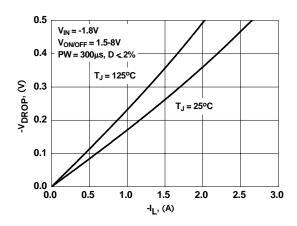


Figure 2. Conduction Voltage Drop Variation with Load Current.

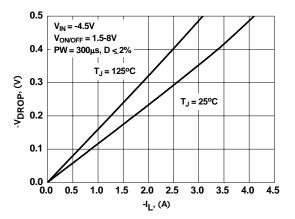


Figure 4. Conduction Voltage Drop Variation with Load Current.

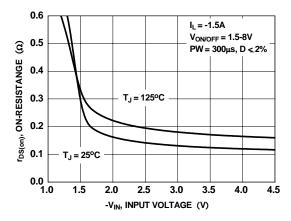


Figure 6. On-Resistance Variation
With Input Voltage





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